SILICON PLANAR EPITAXIAL TRANSISTORS

PNP medium power transistors in a microminiature SMD package (SOT-223). Designed primarily for high-speed switching and driver applications.

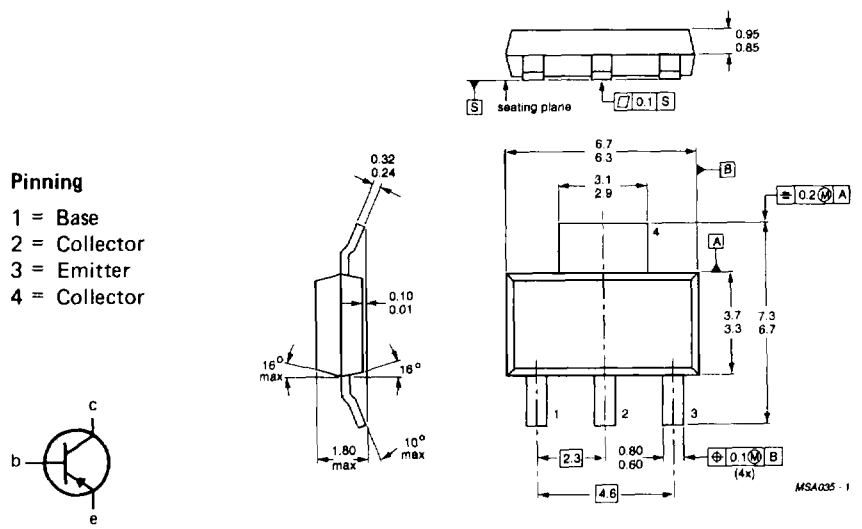
QUICK REFERENCE DATA

Collector-base voltage (open emitter)		$-V_{CBO}$	max.	60 V
Collector-emitter voltage (open base)	**PZT2907**	$-V_{CEO}$	max.	40 V
	PZT2907A	$-V_{CEO}$	max.	60 V
Collector current (DC)		$-I_C$	max.	600 mA
Total power dissipation up to T_{amb} = 25 °C		P_{tot}	max.	1,5 W
Junction temperature		T_j	max.	150 °C
DC current gain at T_j = 25 °C $-I_C$ = 150 mA; $-V_{CE}$ = 10 V		h_{FE}	100 to 300	
Transition frequency at f = 100 MHz $-I_C$ = 50 mA; $-V_{CE}$ = 20 V; T_j = 25 °C		f_T	min.	200 MHz
Storage time $-I_{Con}$ = 150 mA; $-I_{Bon} = I_{Boff}$ = 15 mA		t_s	max.	80 ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223



Pinning

1 = Base
2 = Collector
3 = Emitter
4 = Collector

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)		$-V_{CBO}$	max.	60 V
Collector-emitter voltage (open base)	**PZT2907**	$-V_{CEO}$	max.	40 V
	PZT2907A	$-V_{CEO}$	max.	60 V
Emitter-base voltage (open collector)		$-V_{EBO}$	max.	5 V
Collector current (DC)		$-I_C$	max.	600 mA
Total power dissipation up to T_{amb} = 25 °C		P_{tot}	max.	1,5 W
Storage temperature range		T_{stg}	−65 to	+150 °C
Junction temperature		T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	83,3 K/W

* Device mounted on an epoxy printed-circuit board 40 mm x 40 mm x 1,5 mm; mounting pad for the collector lead min. 6 cm^2.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PZT2907	PZT2907A	
Collector cut-off current					
I_E = 0; $-V_{CB}$ = 50 V	$-I_{CBO}$	<	20	10	nA
I_E = 0; $-V_{CB}$ = 50 V; T_{amb} = 150 °C	$-I_{CBO}$	<	20	10	μA
+ V_{BE} = 0,5 V; $-V_{CE}$ = 30 V	$-I_{CEX}$	<	50	50	nA
Base current					
+ V_{BE} = 0,5 V; $-V_{CE}$ = 30 V	I_{BEX}	<	50	50	nA
Collector-base breakdown voltage					
open emitter; $-I_C$ = 10 μA	$-V_{(BR)CBO}$	>	60	60	V
Collector-emitter breakdown voltage*					
open base; $-I_C$ = 10 mA	$-V_{(BR)CEO}$	>	40	60	V
Emitter-base breakdown voltage					
open collector; $-I_E$ = 10 μA	$-V_{(BR)EBO}$	>	5	5	V
Saturation voltages*					
$-I_C$ = 150 mA; $-I_B$ = 15 mA	$-V_{CEsat}$	<	0,4	0,4	V
	$-V_{BEsat}$	<	1,3	1,3	V
$-I_C$ = 500 mA; $-I_B$ = 50 mA	$-V_{CEsat}$	<	1,6	1,6	V
	$-V_{BEsat}$	<	2,6	2,6	V
DC current gain					
$-I_C$ = 0,1 mA; $-V_{CE}$ = 10 V	h_{FE}	>	35	75	
$-I_C$ = 1 mA; $-V_{CE}$ = 10 V	h_{FE}	>	50	100	
$-I_C$ = 10 mA; $-V_{CE}$ = 10 V	h_{FE}	>	75	100	
$-I_C$ = 150 mA; $-V_{CE}$ = 10 V*	h_{FE}	>	100	100	
		<	300	300	
$-I_C$ = 500 mA; $-V_{CE}$ = 10 V*	h_{FE}	>	30	50	
Collector capacitance at f = 100 kHz					
$I_E = I_e$ = 0; $-V_{CB}$ = 10 V	C_c	<	8		pF
Emitter capacitance at f = 100 kHz					
$I_C = I_c$ = 0; $-V_{EB}$ = 2 V	C_e	<	30		pF
Transition frequency at f = 100 MHz					
$-I_C$ = 50 mA; $-V_{CE}$ = 20 V*	f_T	>	200		MHz

* Measured under pulse conditions to avoid excessive dissipation: $t_p \leqslant 300$ μs; $\delta \leqslant 0{,}02$.

Turn-on time (see Fig. 2)
when switched to $-I_{Con}$ = 150 mA; $-I_{Bon}$ = 15 mA

delay time	t_d	<	10 ns
rise time	t_r	<	40 ns
turn-on time	t_{on}	<	45 ns

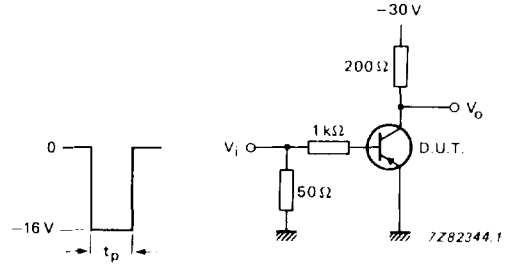


Fig. 2 Input waveform and test circuit for determining delay, rise and turn-on time.

Turn-off time (see Fig. 3)
when switched from $-I_{Con}$ = 150 mA; $-I_{Bon}$ = 15 mA
to cut-off with + I_{Boff} = 15 mA

storage time	t_s	<	80 ns
fall time	t_f	<	30 ns
turn-off time	t_{off}	<	100 ns

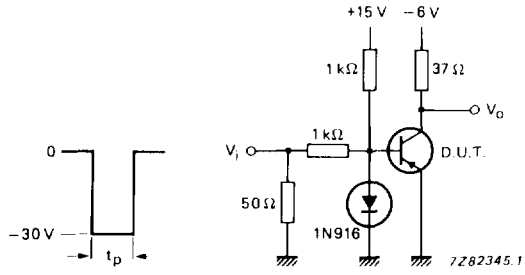


Fig. 3 Input waveform and test circuit for determining storage, fall and turn-off time.

Pulse generator (see Figs 2 and 3)

frequency	f	=	150 Hz
pulse duration	t_p	=	200 ns
rise time	t_r	≤	2 ns
output impedance	Z_o	=	50 Ω

Oscilloscope (see Figs 2 and 3)

rise time	t_r	≤	5 ns
input impedance	Z_i	≤	10 MΩ